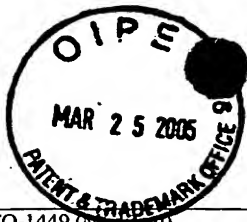

James P. Zeller

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INFORMATION DISCLOSURE STATEMENT		Applicant Gogolides et al.	
		Filing Date May 30, 2003	Group

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
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	International Search Report in PCT/GB03/00018 dated September 23, 2003

Examiner	Date Considered
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	